MILITARY SPECIFICATION

SEMICONDUCTOR DEVICE, TRANSISTOR, PNP, GERMANIUM, HIGH-POWER TYPE 2N297A

This specification is mandatory for use by all Departments and Agencies of the Department of Defense.

1. SCOPE

- 1.1 Scope. This specification covers the detail requirements for a PNP, germanium, high-power transistor.
 - 1.2 Physical dimensions. See figure 1.
 - 1.3 Maximum ratings.

P _T 1/	v _{сво}	V _{EBO}	V _{CES}	v _{CEO}	I _E	T _{stg}
w	Vdc	Vdc	<u>Vdc</u>	<u>Vdc</u>	<u>Adc</u>	<u>°C</u>
50	-80	-40	-70	-40	5. 0	-65 to +100

^{1/} Derate 0.67 W/°C for $T_{MB} > 25$ ° C.

1.4 Primary electrical characteristics.

	h _{FE}	h _{FE}	V _{CE} (sat)	^θ J-C	^f hfe
	$V_{CE} = -2.0 \text{ Vdc}$ $I_{C} = -0.5 \text{ Adc}$	$V_{CE} = -2.0 \text{ Vdc}$ $I_{C} = -2.0 \text{ Adc}$	I _C = -2.0 Adc I _B = -200 mAdc		V _{CE} = -14 Vdc I _C = -0.5 Adc
			<u>Vdc</u>	°C/W	<u>kHz</u>
Min	40	30			5.0
Max	100		-0.7	1.5	

2. APPLICABLE DOCUMENTS

2.1 The following documents, of the issue in effect on date of invitation for bids or request for proposal, form a part of this specification to the extent specified herein.

SPECIFICATION

MILITARY

MIL-S-19500 - Semiconductor Devices, General Specification for

FSC 5961

STANDARDS

MILITARY

MIL-STD-202 - Test Methods for Electronic and Electrical Component Parts.

MIL-STD-750 - Test Methods for Semiconductor Devices.

(Copies of specifications, standards, drawings, and publications required by suppliers in connection with specific procurement functions should be obtained from the procuring activity or as directed by the contracting officer.)

3. REQUIREMENTS

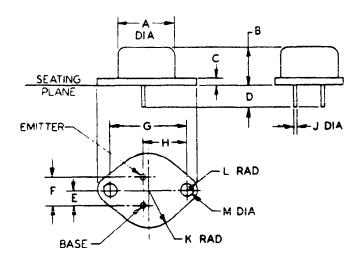
- 3.1 General. Requirements shall be in accordance with MIL-S-19500, and as specified herein,
- 3.2 Abbreviations, symbols, and definitions. The abbreviations, symbols, and definitions used herein are defined in MIL-S-19500, and as follows:

 $T_{\mbox{\scriptsize MB}}$ Mounting base temperature

- 3.3 Design, construction, and physical dimensions. The transistor shall be of the design, construction, and physical dimensions specified in figure 1.
- 3.4 Performance characteristics. Performance characteristics shall be as specified in tables I, II, and $\overline{\text{III}}$.
- 3.5 Marking. The following marking specified in MIL-S-19500 may be omitted from the body of the transistor at the option of the manufacturer:
 - (a) Country of origin.
 - (b) Manufacturer's identification.

4. QUALITY ASSURANCE PROVISIONS

- 4.1 Sampling and inspection. Sampling and inspection shall be in accordance with MIL-S-19500, and as specified herein.
- 4.2 Qualification inspection. Qualification inspection shall consist of the examinations and tests specified in tables I, Π , and $\overline{\Pi}$.
- 4.3 Quality conformance inspection. Quality conformance inspection shall consist of groups A, B, and C inspections.
- 4.3.1 Group A inspection. Group A inspection shall consist of the examinations and tests specified in table I.
- 4.3.2 Group B inspection. Group B inspection shall consist of the examinations and tests specified in table Π .
- 4.3.3 Group C inspection. Group C inspection shall consist of the examinations and tests specified in table III. This inspection shall be conducted on the initial lot and thereafter every 6 months during production.
- 4.3.4 Group B and group C life-test samples. Samples that have been subjected to group B, 340-hours life-test, may be continued on test for 1,000-hours in order to satisfy group C life-test requirements. These samples shall be predesignated, and shall remain subjected to the group C 1,000-hour acceptance evaluation after they have passed the group B, 340-hour acceptance criteria. The cumulative total of failures found during 340-hour test and during the subsequent interval up to 1,000 hours, shall be computed for 1,000-hour acceptance criteria.



LTR	INC	CHES	MILLD	MILLIMETERS			
ļ	MIN	MAX	MIN	MAX			
A		. 875		22.23			
В		. 562		14.27			
C		. 135		3.43			
D	. 312		7.92		3		
E	. 205	. 225	5.21	5.72			
F	. 420	. 440	10.67	11.18			
G	1.177	1.197	29.90	30.40			
H	. 655	. 675	16.64	17.15	2		
J	.038	. 043	. 97	1.09	3		
K		. 525		13.34			
L		. 188		4.78			
M	. 151	. 161	3.84	4.09			

NOTES:

- 1. Metric equivalents (to the nearest .01 mm) are given for general information only and are based upon 1 inch = 25.4 mm.
- This dimension should be measured at points .050 (1.27 mm) to .055 (1.40 mm) below seating plane. When gage is not used, measurement will be made at seating plane. Two leads.
- Collector shall be electrically connected to the case.

FIGURE 1. Physical dimensions of transistor type 2N297A.

TABLE I. Group A inspection

		MIL-STD-750				Limits	
Examination or test	Method	Details	LTPD	Symbol	Min	Max	Unit
Subgroup 1			5				
Visual and mechanical exam- ination	2071						
Subgroup 2			5				
Breakdown voltage, collector to emitter	3011	Bias cond. D; I _C = -300 mAdc		BVCEO	-40		Vdc
Breakdown voltage, collector to emitter	3011	Bias cond. C; I _C = -300 mAdc		BVCES	-70		Vdc
Collector to base cutoff cur- rent	3036	Bias cond. D; V _{CB} = -2.0 Vdc		I _{CBO}		-150	μ Ad c
Collector to base cutoff cur- rent	3036	Bias cond. D; V _{CB} = -80 Vdc		ГСВО		-3.0	mAdc
Emitter to base cutoff current	3061	Bias cond. D; V _{EB} = -40 Vdc		I _{EBO}		-1.0	mAdc
Subgroup 3			5				
Forward-current transfer ratio	3076	$V_{CE} = -2.0 \text{Vdc}; I_{C} = -0.5 \text{Add}$	}	h _{FE}	40	100	
Forward-current transfer ratio	3076	$V_{CE} = -2.0 \text{Vdc}; I_{C} = -2.0 \text{Add}$!	h _{FE}	30		
Collector to emitter voltage (saturated)	3071	$I_{\rm C}$ = -2.0 Adc; $I_{\rm B}$ = -200 mAdc	:	VCE ^(sat)		-0.7	:
Base-emitter voltage (saturated)	3066	Test cond. A; I _C = -2.0 Adc; I _B = -200 mAdc		V _{BE} (sat)		-1.0	Vdc
Base-emitter voltage (nonsaturated)	3066	Test cond. B; V _{CE} = -2.0 Vdc; I _C = -2.0 Adc		v_{BE}		-1.5	Vdc
Subgroup 4			15			1	•
Small-signal short-circuit forward-current transfer ratio cutoff frequency	3301	$V_{CE} = -14 \text{ Vdc}; I_{C} = -0.5 \text{ Adc}$: 	f _{nfe}	5.0		kHz
High-temperature operation:		T _{MB} = + 85° C				1	ļ
Collector to base cutoff current	3036	Bias cond. D; V _{CB} = -40 Vdc	1	ІСВО		-8. 0	m Ad c
Low-temperature operation:		T _{MB} = -55° C	i				
Forward-current transfer ratio	3076	$V_{CE} = -2.0 \text{ Vdc}; I_{C} = -0.5 \text{ Adc}$		hFE	30		
L	L			<u> </u>			

TABLE II. Group B inspection

		MIL-STD-750				Limits	
Examination or test	Method	Details	LTPD	Symbol	Min	Max	Unit
Subgroup 1			20				
Physical dimensions	2066	(See figure 1)					
Subgroup 2			15				
Solderability	2026	Omit aging					
Thermal shock (temperature cycling)	1051	Test cond. A		•••			
Thermal shock (glass strain)	1056	Test cond. B					
Terminal strength (tension)	2036	Test cond. A; weight = 21 lbs; time = 15 sec to each terminal					
Terminal strength (terminal torque)	2036	Test cond. D1; torque = 6 in oz.; t = 15 sec to each ter- minal					
Seal (leak-rate)		Method 112, MIL-STD-202, test cond. C, procedure III; test cond. B for gross leaks				5x10 ⁻⁷	atm cc/sec
isture resistance	1021	Omit initial conditioning					
End points:							
Emitter to base cutoff current	3061	Bias cond. D; V _{EB} = -40 Vdc		I _{EBO}		-1.0	mAdc
Collector to base cutoff current	3036	Bias cond. D; V _{CB} = -80 Vdc		ІСВО		-3.0	mAdc
Forward-current transfer ratio	3076	V _{CE} = -2.0 Vdc; I _C = -2.0 Adc		hFE	30		
Subgroup 3			15				
Shock	2016	Nonoperating; 1500 G; 0.5 msec; 5 blows in each orientation: X ₁ , Y ₁ , Y ₂ , and Z ₁					
Vibration fatigue	2046	Nonoperating					
Vibration, variable frequency	2056						
Constant acceleration	2006	10, 000 G; in each orientation	n:				
End points: (Same as subgroup 2)		$X_1, Y_1, Y_2, \text{ and } Z_1$					
Subgroup 4			15				1
Salt atmosphere (corrosion)	1041	:				!	
nd point: (Same as subgroup 2)							

TABLE II. Group B inspection - Continued

	MIL-STD-750				Limit		
Examination or test	Method	Details	LTPD	Symbol	Min	Max	Unit
Subgroup 5			7				
High-temperature life (nonoperating)	1031	T _{Stg} = + 100°C; time = 340 hours (see 4.3.4)					
End points:							
Emitter to base cutoff current	3061	Bias cond. D; V _{EB} = -40 Vdc		IEBO		-2.0	m.Ad
Collector to base cutoff current	3036	Bias cond. D; V _{CB} = -80 Vdc		ГСВО		-6.0	mAd
Forward-current transfer ratio	3076	$V_{CE} = -2.0 \text{ Vdc}; I_{C} = -2.0 \text{ Add}$	c	hFE	22		
Subgroup 6			10				
Steady state operation life	1026	$V_{CB} = -20 \text{ Vdc}; T_{MB} = +85^{\circ} \text{ C}$ $P_{T} = 10 \text{ W}; \text{ time} = 340 \text{ hours}$	7				
End points: (Same as subgroup 5)		(see 4.3.4)					

TABLE III. Group C inspection

	MIL-STD-750					Limits	
Examination or test	Method	Details	LTPD	Symbol	Min	Max	Unit
Subgroup 1 Barometric pressure, reduced (altitude operation)	1001	Normal mounting; pressure = 8 mm Hg for 60 sec min	20				
Measurement during test: Collector to base cutoff current	3036	Bias cond. D; V _{CB} = -80 Vdc		ІСВО		-3.0	
Thermal resistance	3151			θЈ-С		1.5	°C/W
Floating potential	3020	V _{CB} = -80 Vdc; voltmeter input resistance > 10 megohms	;	VEBF		-0.18	Vdc
Subgroup 2 High-temperature life (nonoperating) End points: (same as subgroup 5 of	1031	T _{stg} = + 100° C (see 4.3.4)	λ = 10				
group B)		: :					

TABLE III. Group C inspection - Continued

	MIL-STD-750					Limits	5
Examination or test	Method	Details	LTPD	Symbol	Min	Max	Unit
Subgroup 3			λ = 15				
Steady state operation life	1026	V _{CB} = -20 Vdc; T _{MB} = +85°C; P _T = 10 W					
End points: (Same as subgroup 5 of group B)		(see 4.3.4)					

- 5. PREPARATION FOR DELIVERY
- 5.1 See MIL-S-19500, section 5.
- 6. NOTES
- 6.1 Notes. The notes specified in MIL-S-19500 are applicable to this specification.
- 6.2 Changes from previous issue. Asterisks are not used in this revision to identify changes with respect to the previous issue, due to the extensiveness of the changes.

Custodians

Army - EL

Navy - SH

Air Force - 11

Preparing activity: Army - EL

(Project 5961-0008-11)

Review activities:

Army - EL, MU, MI

Navy - SH

Air Force - 11, 17, 85

Code "C"

User activities:

Army - EL, SM Navy - CG, MC, AS, OS Air Force - 14, 19

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